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March 2011

MPSA06 / MMBTA06 / PZTA06 NPN General Purpose Amplifier

Features

- This device is designed for general purpose amplifier applications at collector currents to 300mA.
- Sourced from Process 33.



Absolute Maximum Ratings * T_a = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	80	V
V_{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	4.0	V-10
I _C	Collector Current - Continuous	500	mA
T _{J.} T _{stq}	Operating and Storage Junction Temperature Range	- 55 to +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics $T_a = 25^{\circ}$ C unless otherwise noted

Symbol	Parameter	Max.			Units
		MPSA06	*MMBTA06	**PZTA06	Uillis
P _D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/°C
$R_{ heta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

^{*} Device mounted on FR-4 PCB 1.6" \times 1.6" \times 0.06".

^{**} Device mounted on FR-4 PCB 36mm \times 18mm \times 1.5mm; mounting pad for the collector lead min. 6cm 2 .

W.100Y.COM.TW Electrical Characteristics T_a = 25°C unless otherwise noted

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Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Character	ristics	W. 100	CON	1.1	·
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage* I _C = 1.0mA, I _B = 0		80	WILL	V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	4.0	WILL	V
I _{CEO}	O Collector-Cutoff Current $V_{CE} = 60V, I_B = 0$. any.C	0.1	μΑ
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 80V, I_{E} = 0$	100	0.1	μΑ
On Character	ristics	WITH	N.100 r	COM.	-1
100 hFE	DC Current Gain	$I_C = 10$ mA, $V_{CE} = 1.0$ V $I_C = 100$ mA, $V_{CE} = 1.0$ V	100 100	.coM.T	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	tter Saturation Voltage I _C = 100mA, I _B = 10mA		0.25	V
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 100 \text{mA}, V_{CE} = 1.0 \text{V}$	-XXV 101	1.2	V
	Characteristics	WILLIAM V	-x1 10	107.	T.T.W
VW f _T	Current Gain - Bandwidth Product	$I_C = 10 \text{mA}, V_{CE} = 2.0 \text{V},$ f = 100 MHz	100	1001.CO	MHz
Pulse Test: P	ulse Width ≤ 300μs, Duty Cycle ≤ 2.0%	Ox. COM.T.M	W TO	7007.	OM.T

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^{*} Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0% WWW.100Y.COM.TW WWW.100Y.C WWW.100Y.COM.TW

Typical Performance Characteristics

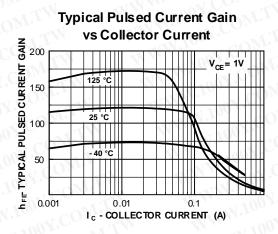


Figure 1. Typical Pulsed Current Gain vs Collector Current

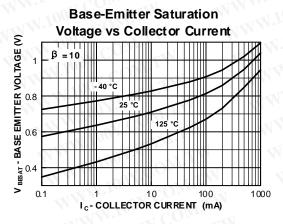


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

Collector-Cutoff Current

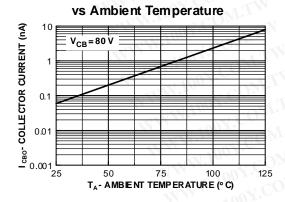


Figure 5. Collector Cutoff Current vs Ambient Temperature

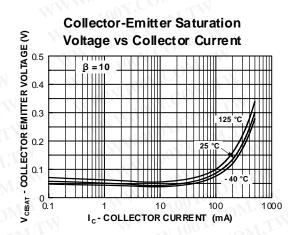


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

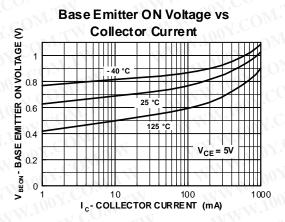


Figure 4. Base-Emitter On Voltage vs Collector Current

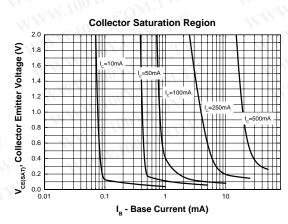


Figure 6. Collector Saturation Region

Typical Performance Characteristics (continued)

Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base 117 116 118 119 119 110 110 100 1000 RESISTANCE (kΩ)

Figure 7. Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base

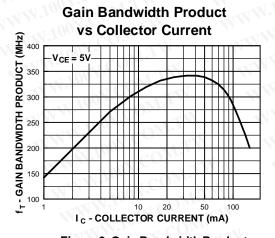


Figure 9. Gain Bandwidth Product vs Collector Current

Input and Output Capacitance vs Reverse Voltage

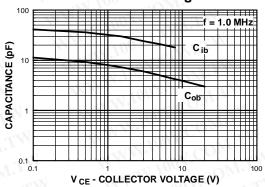


Figure 8. Input and Output Capacitance vs Reverse Voltage

Power Dissipation vs Ambient Temperature

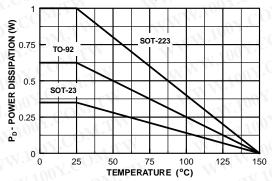


Figure 10. Power Dissipation vs
Ambient Temperature

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